N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

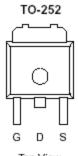
terep	onones.	
•	Low r _{DS(on)} provides higher efficiency and extends battery life	

•	Low thermal impedance copper leadframe
	DPAK saves board space

- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	I _D (A)	
20	$10 @ V_{GS} = 4.5V$	58	
20	$16 @ V_{GS} = 2.5V$	46	





Top View

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage			20	V
Gate-Source Voltage			±8	V
Continuous Drain Current ^a	$T_C=25^{\circ}C$	I_D	58	
Pulsed Drain Current ^b			40	А
Continuous Source Current (Diode Conduction) ^a	I_S	30	A	
Power Dissipation ^a T _C =25°C			50	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{ heta JA}$	50	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

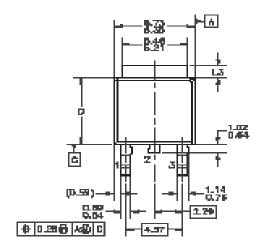
Dawarea 4a u		T. (C. P.)	Limits			TT *4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \ V, \ V_{GS} = 8 \ V$			±100	nA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	1 uA	
Zeio Gate voltage Diain Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^A	ID(on)	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	34			A	
. Δ		$V_{GS} = 4.5 \text{ V}, I_{D} = 51 \text{ A}$			10		
Drain-Source On-Resistance ^A	fDS(on)	$V_{GS} = 2.5 \text{ V}, I_{D} = 41 \text{ A}$			16	mΩ	
Forward Tranconductance ^A	gs	$V_{DS} = 10 \text{ V}, I_D = 51 \text{ A}$		22		S	
Diode Forward Voltage	V_{SD}	$I_S = 34 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 51 \text{ A}$		4.0			
Gate-Source Charge	Qgs			1.1		nC	
Gate-Drain Charge	Qgd			1.4		1 1	
Turn-On Delay Time	t _{d(on)}			16			
Rise Time	t_r	$V_{\rm DD}$ = 15 V, R_L = 25 Ω , $I_{\rm D}$ = 34 A,		5		nS	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}$		23		113	
Fall-Time	tf			3		1	

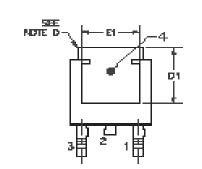
Notes

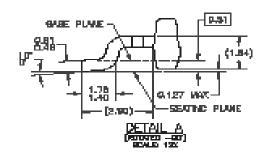
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

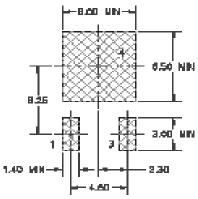
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Package Information

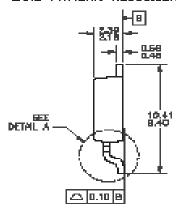








LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

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